

Title (en)

METHOD FOR METALLIZING THE PREVIOUSLY PASSIVATED SURFACE OF A SEMICONDUCTOR MATERIAL AND RESULTING MATERIAL

Title (de)

VERFAHREN ZUR METALLISIERUNG DER ZUVOR PASSIVIERTEN OBERFLÄCHE EINES HALBLEITERMATERIALS UND AUF DIESE WEISE HERGESTELLTES MATERIAL

Title (fr)

PROCEDE DE METALLISATION DE LA SURFACE PREALABLEMENT PASSIVEE D'UN MATERIAU SEMICONDUCTEUR ET MATERIAU OBTENU PAR CE PROCEDE

Publication

**EP 1759406 A1 20070307 (FR)**

Application

**EP 05778242 A 20050620**

Priority

- FR 2005050469 W 20050620
- FR 0406751 A 20040621

Abstract (en)

[origin: WO2006005869A1] The invention concerns a method for metallizing the previously passivated surface of a semiconductor material and resulting material. The invention, which is applicable in microelectronics, is characterized in that it consists in: preparing the surface of the material (2) so that it contains bonds capable of absorbing hydrogen atoms or a metal element, passivating one or more layers, preferably immediately underlying the surface, by exposing same to a passivating compound, and metallizing the surface (4) by exposing same to hydrogen atoms or the metal element.

IPC 8 full level

**H01L 21/285** (2006.01); **H01L 21/04** (2006.01)

CPC (source: EP US)

**H01L 21/045** (2013.01 - EP US); **H01L 21/0485** (2013.01 - EP US); **H01L 21/28512** (2013.01 - EP US); **H01L 2924/0002** (2013.01 - EP US); **Y10T 428/31678** (2015.04 - EP US)

C-Set (source: EP US)

**H01L 2924/0002 + H01L 2924/00**

Citation (search report)

See references of WO 2006005869A1

Designated contracting state (EPC)

AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HU IE IS IT LI LT LU MC NL PL PT RO SE SI SK TR

DOCDB simple family (publication)

**FR 2871936 A1 20051223; FR 2871936 B1 20061006; EP 1759406 A1 20070307; JP 2008503889 A 20080207; US 2008026231 A1 20080131; WO 2006005869 A1 20060119**

DOCDB simple family (application)

**FR 0406751 A 20040621; EP 05778242 A 20050620; FR 2005050469 W 20050620; JP 2007517381 A 20050620; US 63045205 A 20050620**